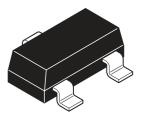


# ZXTP25012EFH 12V, SOT23, PNP medium power transistor

## Summary

 $BV_{CEO} > -12V$   $h_{FE} > 500$   $I_{C(cont)} = 4A$   $R_{CE(sat)} = 40m\Omega$   $V_{CE(sat)} < -65mV @ 1A$  $P_D = 1.25W$ 



Complementary part number ZXTN25012EFH

## Description

Advanced process capability and package design have been used to maximise the power handling and performance of this small outline transistor. The compact size and ratings of this device make it ideally suited to applications where space is at a premium.

### Features

- High power dissipation SOT23 package
- High peak current
- Very high gain, 500 minimum
- Low saturation voltage

## Applications

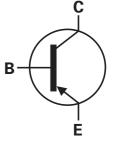
- MOSFET and IGBT gate driving
- DC DC converters
- Motor drive
- · High side driver
- · Line disconnect switch

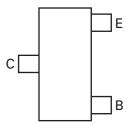
## **Ordering information**

Device	Reel size	Tape width	Quantity
	(inches)	(mm)	per reel
ZXTP25012EFHTA	7	8	3000

## **Device marking**

1E8





Pinout - top view

## Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Collector-base voltage	V <sub>CBO</sub>	-12	V
Collector-emitter voltage	V <sub>CEO</sub>	-12	V
Emitter-base voltage	V <sub>EBO</sub>	-7	V
Continuous collector current <sup>(b)</sup>	Ι <sub>C</sub>	-4	А
Base current	Ι <sub>Β</sub>	-1	А
Peak pulse current	I <sub>СМ</sub>	-10	А
Power dissipation at T <sub>amb</sub> =25°C <sup>(a)</sup>	P <sub>D</sub>	0.73	W
Linear derating factor		5.84	mW/°C
Power dissipation at T <sub>amb</sub> =25°C <sup>(b)</sup>	PD	1.05	W
Linear derating factor		8.4	mW/°C
Power dissipation at T <sub>amb</sub> =25°C <sup>(c)</sup>	PD	1.25	W
Linear derating factor		9.6	mW/°C
Power dissipation at T <sub>amb</sub> =25°C <sup>(d)</sup>	PD	1.81	W
Linear derating factor		14.5	mW/°C
Operating and storage temperature range	T <sub>j</sub> , T <sub>stg</sub>	-55 to 150	°C

### Thermal resistance

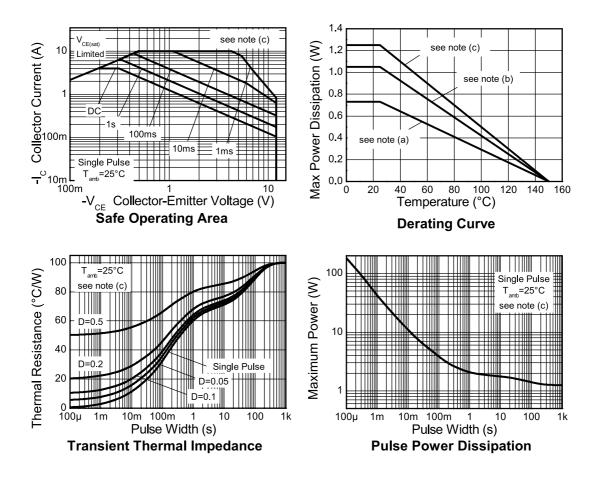
Parameter	Symbol	Limit	Unit
Junction to ambient <sup>(a)</sup>	$R_{\Theta JA}$	171	°C/W
Junction to ambient <sup>(b)</sup>	$R_{\ThetaJA}$	119	°C/W
Junction to ambient <sup>(c)</sup>	$R_{\ThetaJA}$	100	°C/W
Junction to ambient <sup>(d)</sup>	$R_{\ThetaJA}$	69	°C/W

#### NOTES:

(a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

(b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2 oz copper in still air conditions. (d) As (c) above measured at t<5secs

## Characteristics



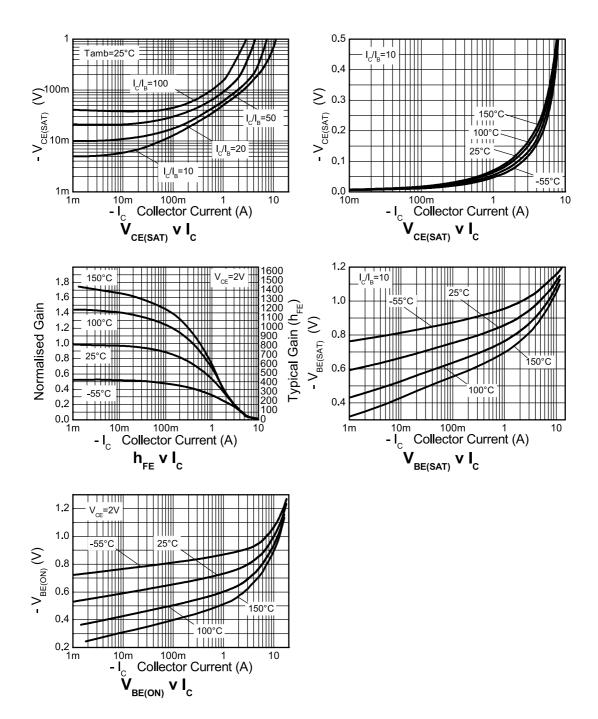
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV <sub>CBO</sub>	-12	-35		V	I <sub>C</sub> = -100μA
Collector-emitter breakdown voltage (base open)	BV <sub>CEO</sub>	-12	-25		V	I <sub>C</sub> = -10mA <sup>(*)</sup>
Emitter-base breakdown voltage	BV <sub>EBO</sub>	-7	-8.5		V	I <sub>E</sub> = -100μA
Collector-base cut-off	I <sub>CBO</sub>		<-1	-50	nA	V <sub>CB</sub> = -12V
current				-0.5	μA	$V_{CB}$ = -12V, $T_{amb}$ = 100°C
Emitter-base cut-off current	I <sub>EBO</sub>		<-1	-50	nA	V <sub>EB</sub> = -5.6V
Collector-emitter saturation	$V_{CE(sat)}$		-50	-65	mV	$I_{C} = -1A, I_{B} = -100 \text{mA}^{(*)}$
voltage			-150	-260	mV	I <sub>C</sub> = -1A, I <sub>B</sub> = -10mA <sup>(*)</sup>
			-175	-350	mV	$I_{C} = -2A, I_{B} = -40mA^{(*)}$
			-160	-210	mV	$I_{C} = -4A, I_{B} = -400 \text{mA}^{(*)}$
Base-emitter saturation voltage	V <sub>BE(sat)</sub>		-970	-1050	mV	$I_{\rm C}$ = -4A, $I_{\rm B}$ = -400mA <sup>(*)</sup>
Base-emitter turn-on voltage	V <sub>BE(on)</sub>		-825	-950	mV	$I_{C} = -4A, V_{CE} = -2V^{(*)}$
Static forward current transfer ratio	h <sub>FE</sub>	500	800	1500		$I_{C} = -10 \text{mA}, V_{CE} = -2V^{(*)}$
transfer ratio		300	450			$I_{C} = -1A, V_{CE} = -2V^{(*)}$
		50	100			$I_{C} = -4A, V_{CE} = -2V^{(*)}$
Transition frequency	f <sub>T</sub>		310		MHz	I <sub>C</sub> = -50mA, V <sub>CE</sub> = -10V f = 100MHz
Output capacitance	C <sub>obo</sub>		16.9		pF	V <sub>CB</sub> = -10V, f = 1MHz <sup>(*)</sup>
Delay time	t <sub>d</sub>		41		ns	V <sub>CC</sub> = -10V
Rise time	t <sub>r</sub>		62		ns	I <sub>C</sub> = -1A, I <sub>B1</sub> = I <sub>B2</sub> = -10mA
Storage time	t <sub>s</sub>		179		ns	
Fall time	t <sub>f</sub>		65		ns	

## Electrical characteristics (at $T_{amb}$ = 25°C unless otherwise stated)

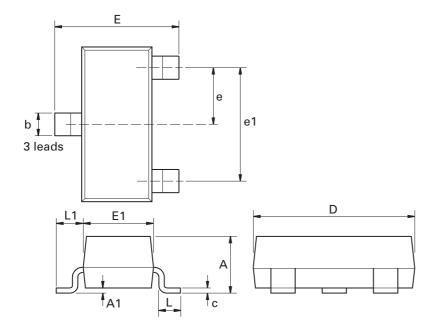
NOTES:

(\*) Measured under pulsed conditions. Pulse width  ${\leq}300\mu s;$  duty cycle  ${\leq}2\%.$ 

## **Typical characteristics**



## Package outline - SOT23



Dim.	Millin	neters	Inc	hes	Dim.	Dim. Millimeters		Inches	
	Min.	Max.	Min.	Max.		Min.	Max.	Max.	Max.
А	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.120	0.003	0.008	L	0.25	0.62	0.018	0.024
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.0375	5 NOM	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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